

## aAs Wafers



### Specifications

Diameter, mm	100
Thickness, $\mu\text{m}$	450; 625
Deviation from nominal value, $\mu\text{m}$	$\pm 25$
Crystallographic orientation, $^\circ$	(100); (100)+10 $^\circ$ ; (111) A
Conductivity type	N
Flat orientation	SEMI E1
Polishing	Double-sided
Dopant	Si
Large carrier mobility, $\text{cm}^2/\text{V}\cdot\text{sec}$	> 1200
Large carrier concentration, $\text{cm}^{-3}$	From $1\cdot 10^{17}$ to $3\cdot 10^{18}$
Dislocation density, $\text{cm}^{-2}$	< 500
TTV minimum, $\mu\text{m}$	2
TTV minimum/standard, $\mu\text{m}$	до 5